

**Features**

- Uses CRM(CQ) advanced SkyMOS1 technology
- Extremely low on-resistance  $R_{DS(on)}$
- Excellent  $Q_g \times R_{DS(on)}$  product(FOM)
- Qualified according to JEDEC criteria

**Product Summary**

$V_{DS}$	100V
$R_{DS(on)}$	3.6mΩ
$I_D$	120A

**Applications**

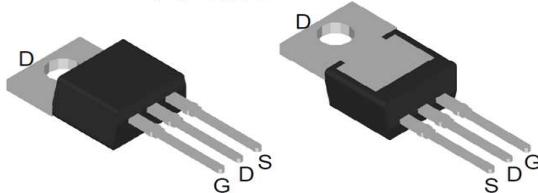
- Motor control and drive
- Battery management
- UPS (Uninterruptible Power Supplies)

100% DVDS Tested

100% Avalanche Tested

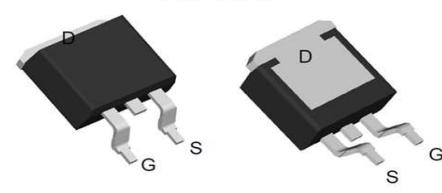


TO-220

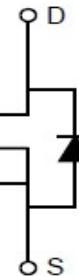


CRST045N10N

TO-263



CRSS042N10N


**Package Marking and Ordering Information**

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRST045N10N	CRST045N10N	TO-220	Tube	N/A	N/A	50pcs
CRSS042N10N	CRSS042N10N	TO-263	Tape	N/A	N/A	1000pcs

**Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	100	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$ (Silicon limit)	$I_D$	172 120 109	A
Pulsed drain current ( $T_C = 25^\circ\text{C}$ , $t_p$ limited by $T_{jmax}$ )	$I_D$ pulse	480	A
Avalanche energy, single pulse ( $L=0.5\text{mH}$ , $R_g=25\Omega$ )	$E_{AS}$	256	mJ
Gate-Source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation ( $T_C = 25^\circ\text{C}$ )	$P_{tot}$	227	W
Operating junction and storage temperature	$T_j$ , $T_{stg}$	-55...+150	°C

**Thermal Resistance**

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R <sub>thJC</sub>	0.55	°C/W
Thermal resistance, junction – ambient(min. footprint)	R <sub>thJA</sub>	62	

**Electrical Characteristic (at T<sub>j</sub> = 25 °C, unless otherwise specified)**

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

**Static Characteristic**

Drain-source breakdown voltage	BV <sub>DSS</sub>	100	115	-	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA
Gate threshold voltage	V <sub>GS(th)</sub>	2	3	4	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA
Zero gate voltage drain current	I <sub>DSS</sub>	-	0.05	1	μA	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V T <sub>j</sub> =25°C T <sub>j</sub> =125°C
Gate-source leakage current	I <sub>GSS</sub>	-	±10	±100	nA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source on-state resistance	R <sub>DS(on)</sub>	-	3.6	4.5	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =50A TO-220 TO-263
Transconductance	g <sub>fs</sub>	-	50	-	S	V <sub>DS</sub> =5V, I <sub>D</sub> =50A

**Dynamic Characteristic**

Input Capacitance	C <sub>iss</sub>	-	6772	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =50V, f=1MHz
Output Capacitance	C <sub>oss</sub>	-	952	-		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	33	-		
Gate Total Charge	Q <sub>G</sub>	-	90	-	nC	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =20A
Gate-Source charge	Q <sub>gs</sub>	-	28	-		
Gate-Drain charge	Q <sub>gd</sub>	-	19	-		
Turn-on delay time	t <sub>d(on)</sub>	-	28	-	ns	V <sub>GS</sub> =10V, V <sub>DD</sub> =50V, R <sub>G_ext</sub> =3.0Ω
Rise time	t <sub>r</sub>	-	32	-		
Turn-off delay time	t <sub>d(off)</sub>	-	48	-		
Fall time	t <sub>f</sub>	-	27	-	Ω	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz
Gate resistance	R <sub>G</sub>	-	2	-		



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CRST045N10N, CRSS042N10N

SkyMOS1 N-MOSFET 100V, 3.6mΩ, 120A

### Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V <sub>SD</sub>	-	0.89	1.3	V	V <sub>GS</sub> =0V, I <sub>SD</sub> =50A
Body Diode Reverse Recovery Time	t <sub>rr</sub>	-	80	-	ns	I <sub>F</sub> =50A, dI/dt=100A/μs
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	-	190	-	nC	

## Typical Performance Characteristics

Fig 1: Output Characteristics

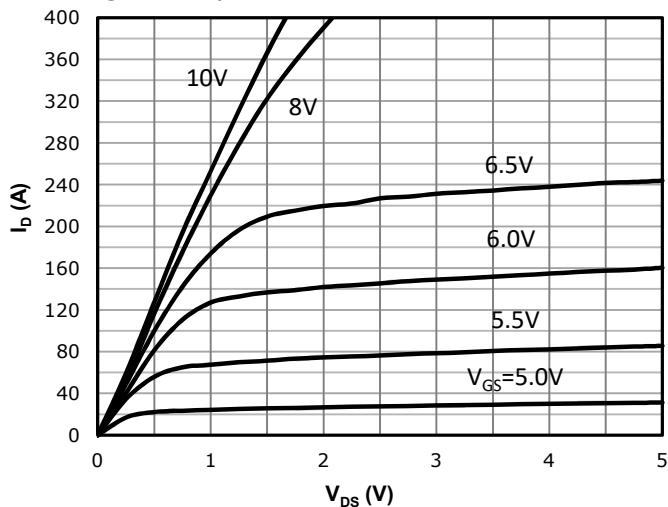


Fig 2: Transfer Characteristics

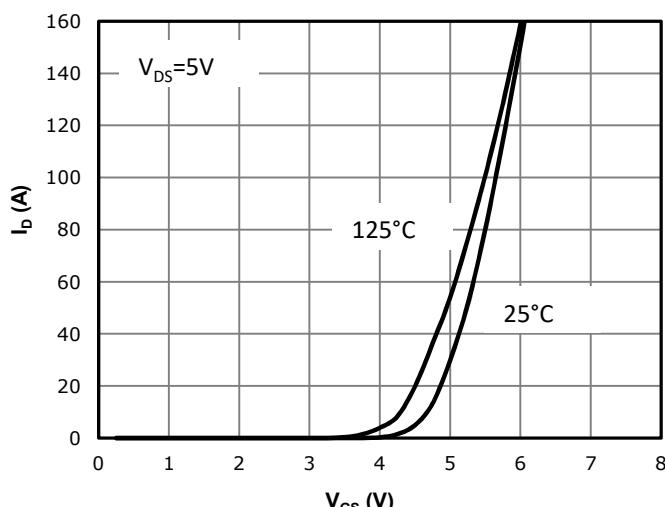
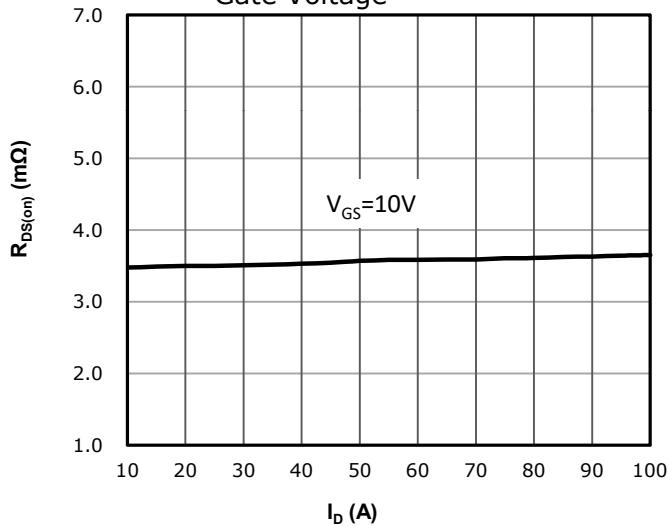
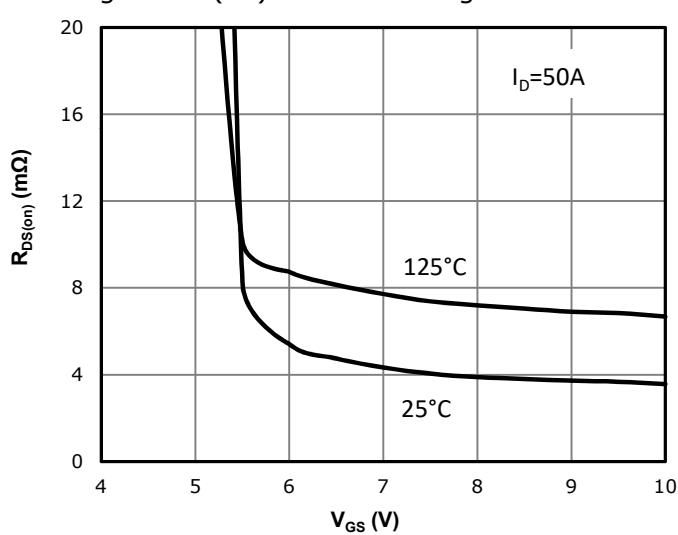
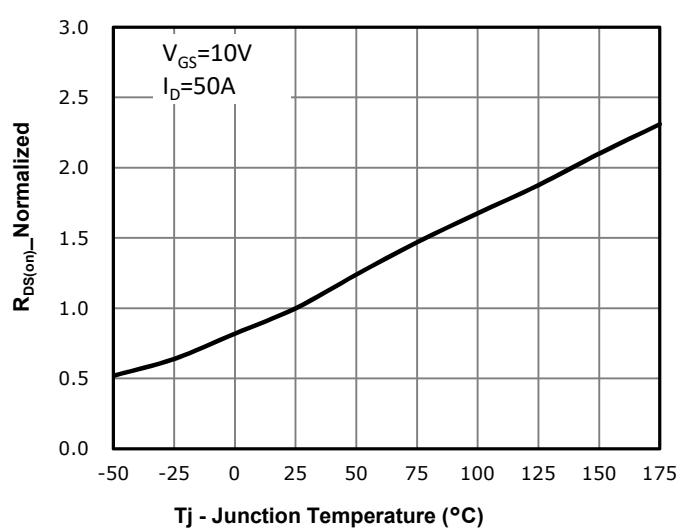

 Fig 3: R<sub>d(on)</sub> vs Drain Current and Gate Voltage

 Fig 4: R<sub>d(on)</sub> vs Gate Voltage

 Fig 5: R<sub>d(on)</sub> vs. Temperature


Fig 6: Capacitance Characteristics

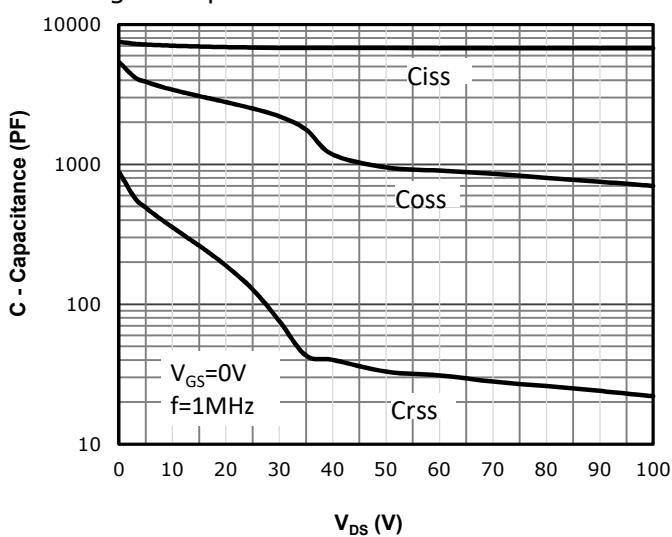


Fig 7: Gate Charge Characteristics

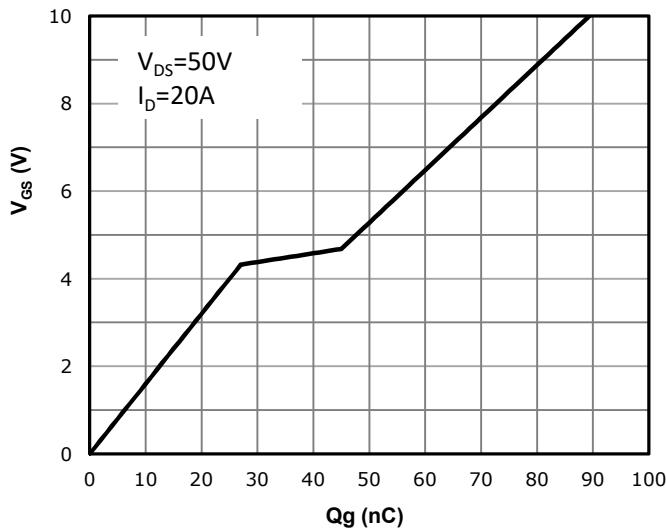


Fig 8: Body-diode Forward Characteristics

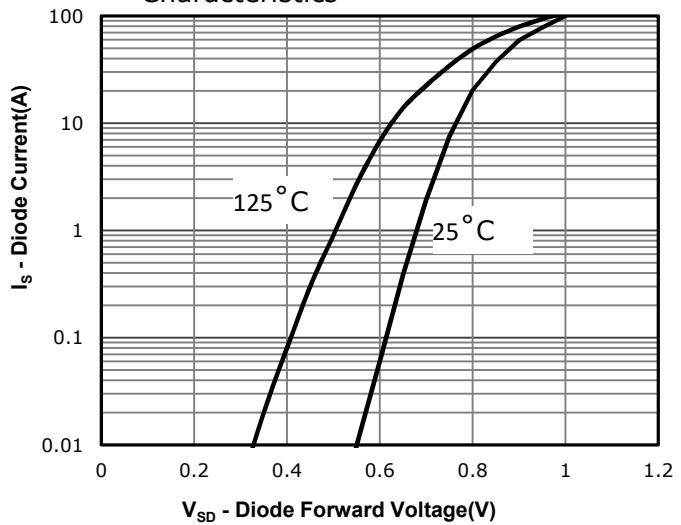


Fig 9: Power Dissipation

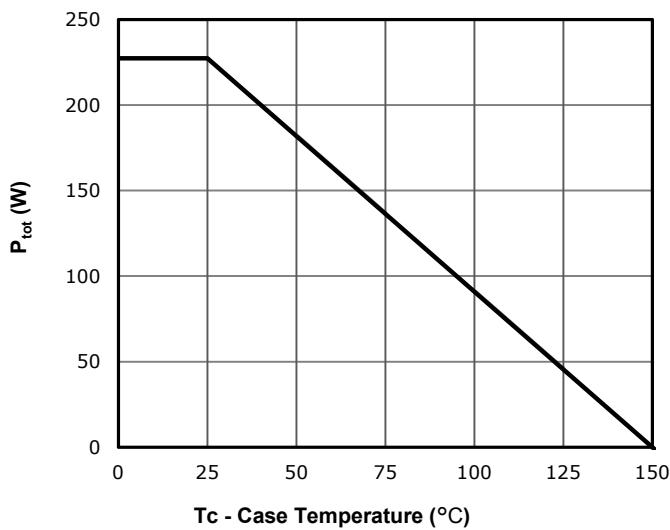


Fig 10: Drain Current Derating

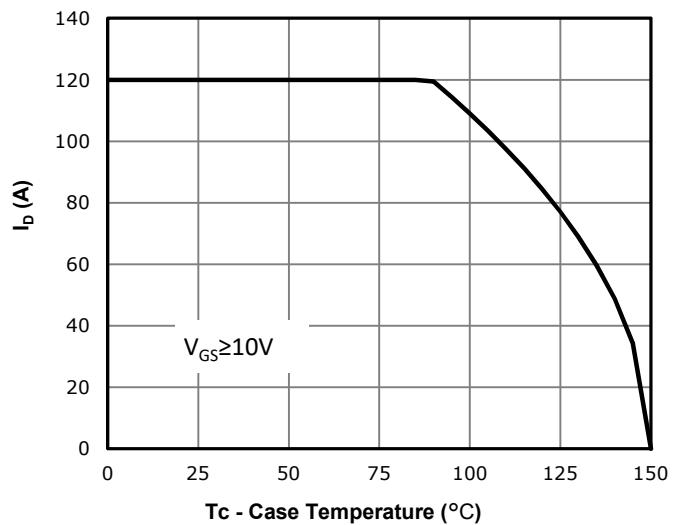


Fig 11: Safe Operating Area

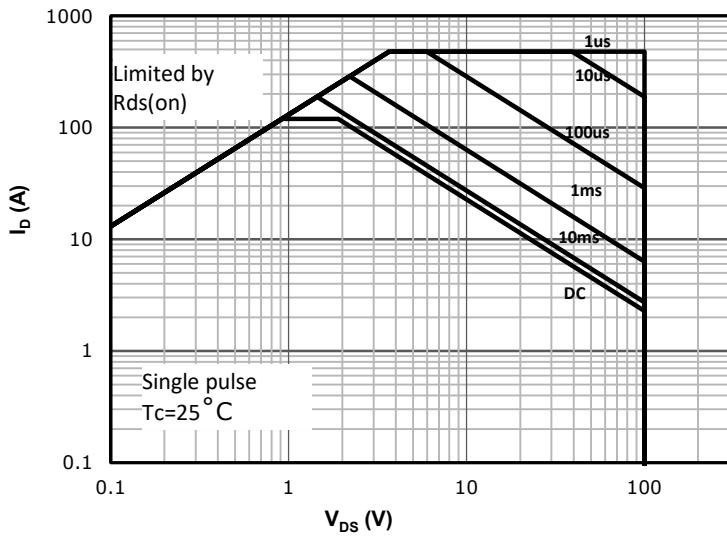
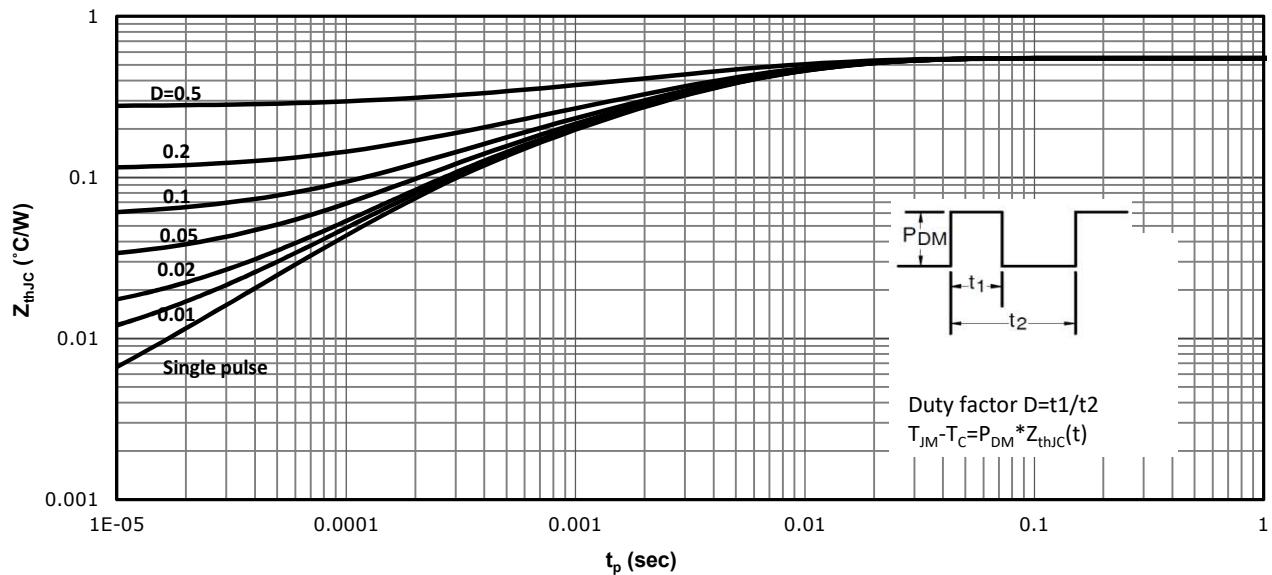
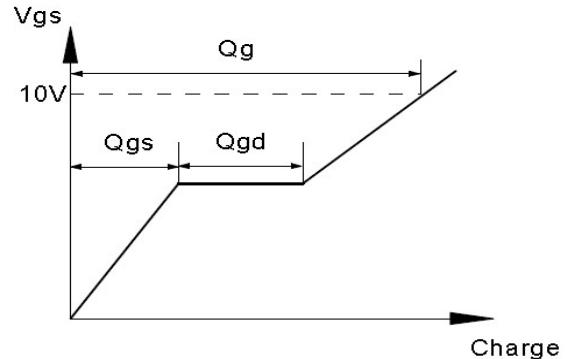
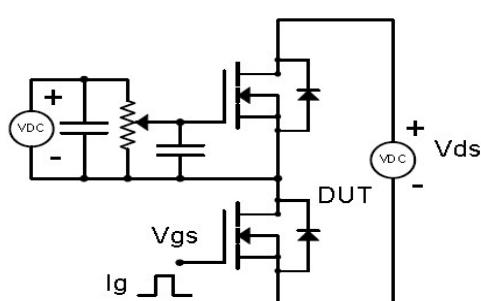


Fig 12: Max. Transient Thermal Impedance

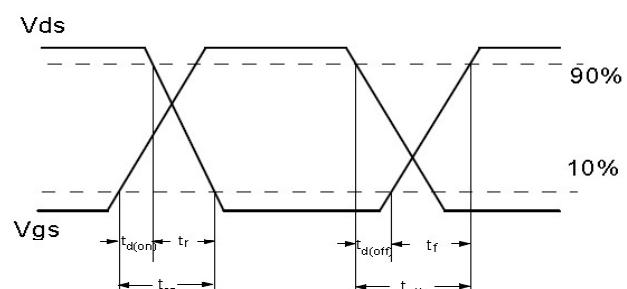
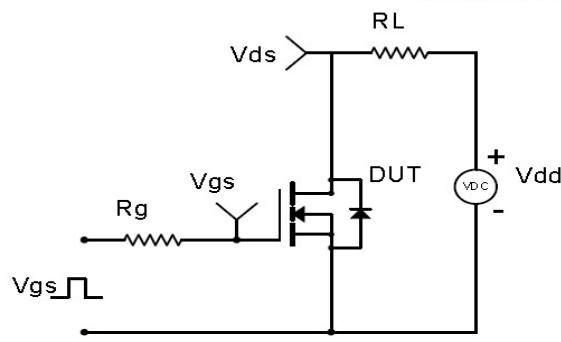


**Test Circuit & Waveform**

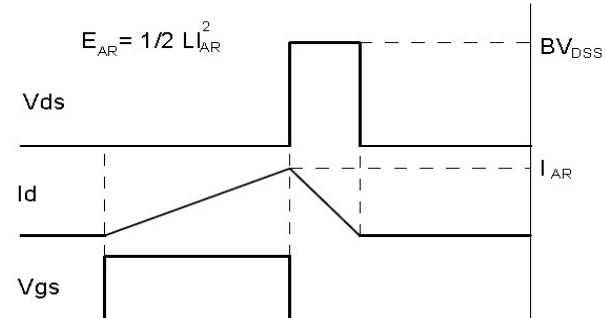
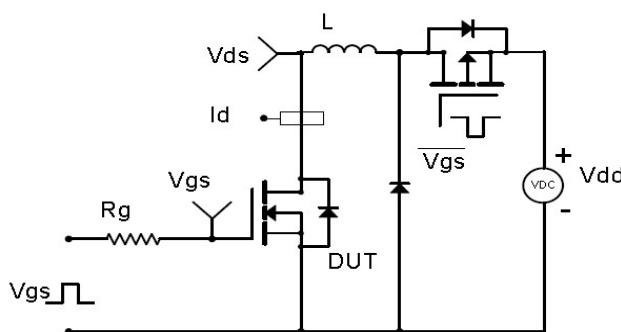
Gate Charge Test Circuit &amp; Waveform



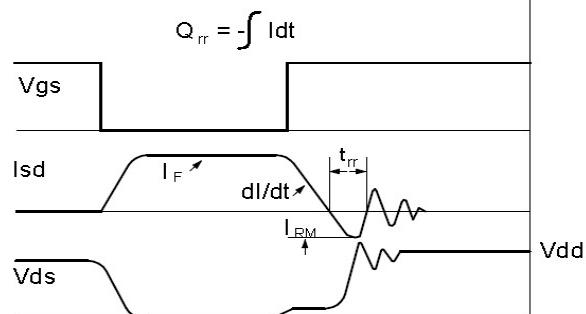
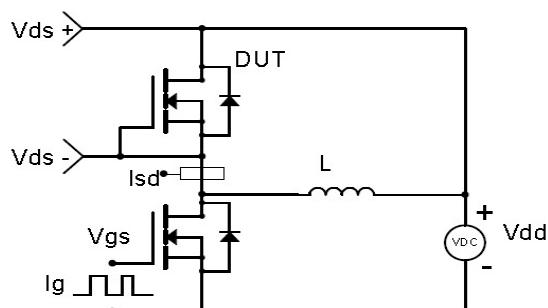
Resistive Switching Test Circuit &amp; Waveforms

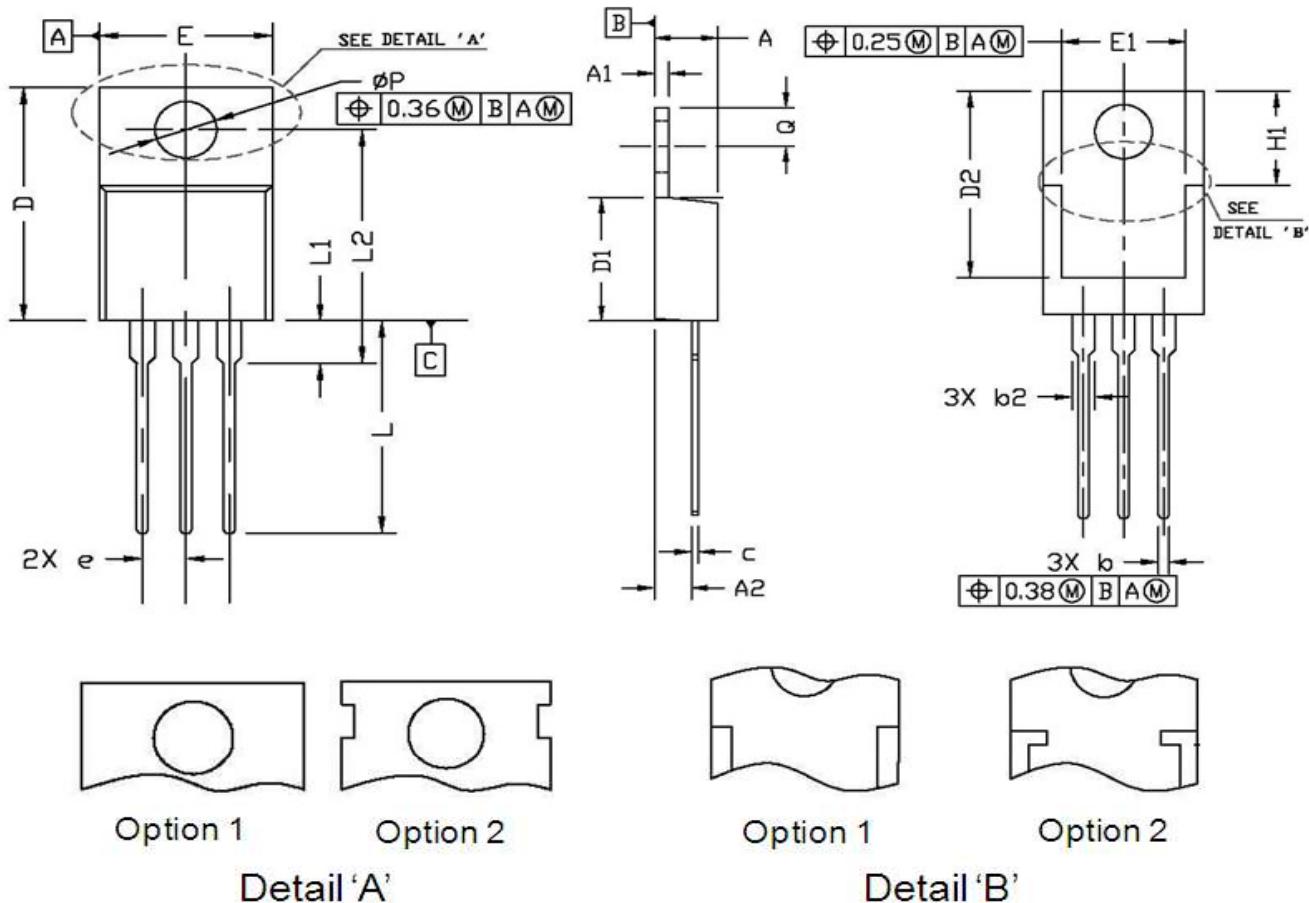


Unclamped Inductive Switching (UIS) Test Circuit &amp; Waveforms

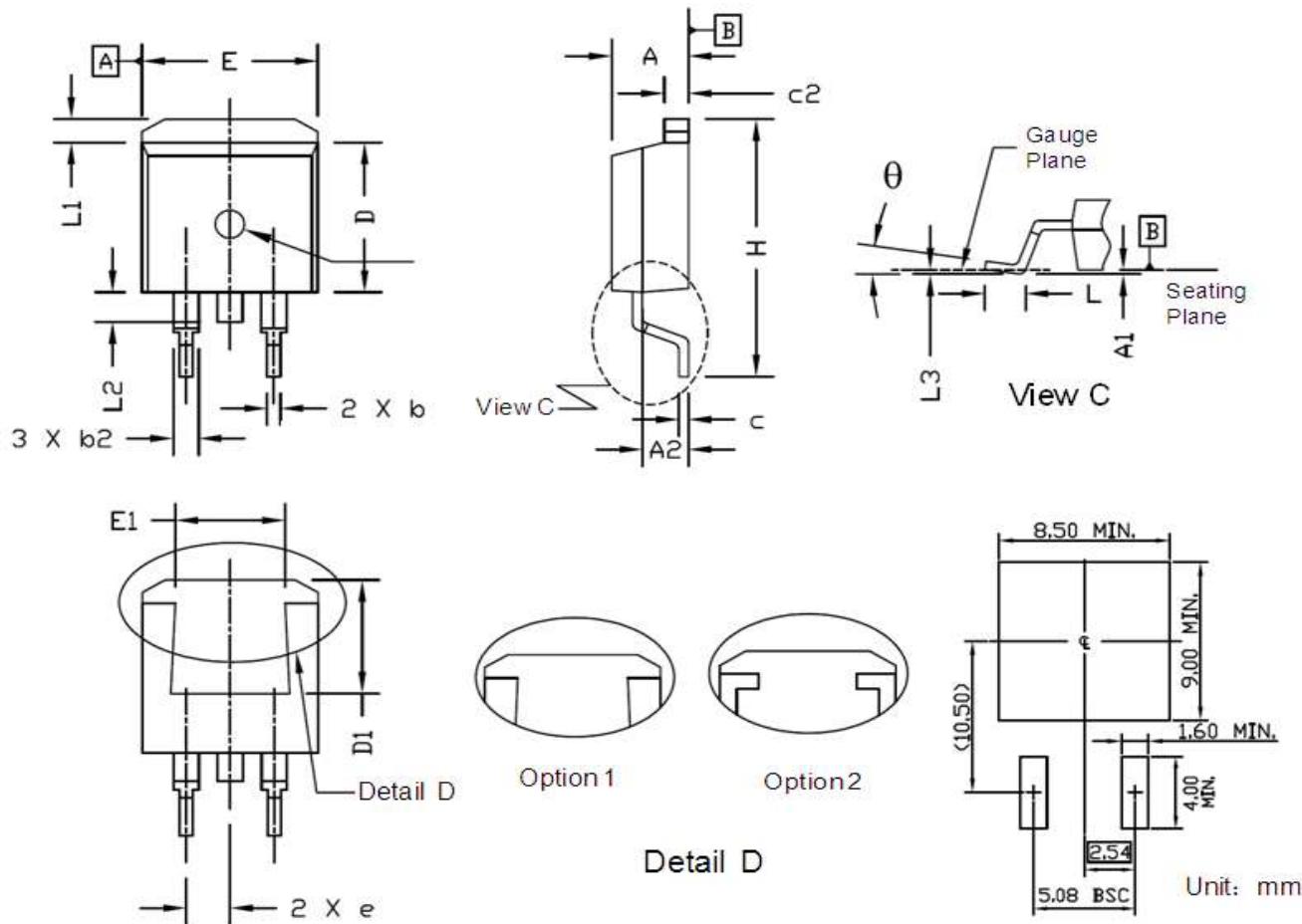


Diode Recovery Test Circuit &amp; Waveforms



**Package Outline: TO-220-3L**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.80	0.169	0.189
A1	1.20	1.45	0.047	0.057
A2	2.20	2.90	0.087	0.114
b	0.69	0.95	0.027	0.037
b2	1.00	1.60	0.039	0.063
c	0.33	0.65	0.013	0.026
D	14.70	16.20	0.579	0.638
D1	8.59	9.65	0.338	0.380
D2	11.75	13.60	0.463	0.535
e	2.54 BSC.		0.100 BSC.	
E	9.60	10.60	0.378	0.417
E1	7.00	8.89	0.276	0.350
H1	6.20	7.00	0.244	0.276
L	12.60	14.80	0.496	0.583
L1	2.70	3.80	0.106	0.150
L2	12.13	16.50	0.478	0.650
Q	2.40	3.10	0.094	0.122
P	3.50	3.95	0.138	0.156

**Package Outline: TO-263**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.86	0.169	0.191
A1	0.00	0.25	0.000	0.010
A2	2.20	2.90	0.087	0.114
b	0.68	0.94	0.027	0.037
b2	1.14	1.78	0.045	0.070
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.38	9.45	0.330	0.372
D1	6.90	8.17	0.272	0.322
e	2.54 BSC.		0.100 BSC.	
E	9.78	10.50	0.385	0.413
E1	6.50	8.60	0.256	0.339
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
L3	0.25 BSC.		0.010 BSC.	
θ	Option A	-8°	0°	-8°
	Option B	0°	8°	0°
				8°



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CRST045N10N, CRSS042N10N

SkyMOS1 N-MOSFET 100V, 3.6mΩ, 120A

## Revision History

Revison	Date	Major changes
1.0	2018/2/9	Release of formal version.
2.0	2019/5/28	Supplement package outline info.
2.1	2022/3/1	Add identification.
3.0	2023/10/28	Package Info Update.

## Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.